## Document Title

**256Kx8 bit Super Low Power and Low Voltage Full CMOS Static RAM**

## Revision History

| Revision No. | History | Draft Date | Remark |
|---|---|---|---|
| 0.0 | Initial Draft | February 28, 2001 | Preliminary |
| 1.0 | Finalize | September 27, 2001 | Final |

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## *256Kx8 bit Super Low Power and Low Voltage Full CMOS Static RAM*

### FEATURES

- Process Technology: Full CMOS
- Organization: 256Kx8
- Power Supply Voltage: 2.3~2.7V
- Low Data Retention Voltage: 1.5V(Min)
- Three State Outputs
- Package Type: 32-TSOP1-0813.4F

### GENERAL DESCRIPTION

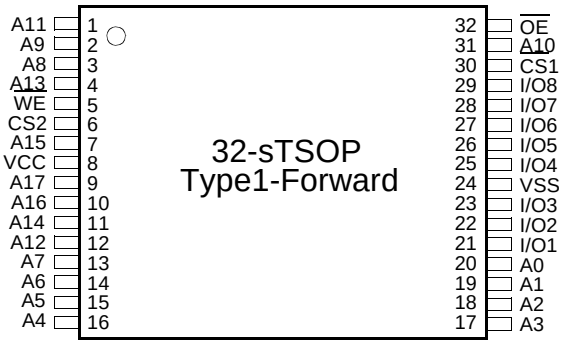
The K6F2008S2E families are fabricated by SAMSUNG′s advanced Full CMOS process technology. The families support various operating temperature ranges and have various package types for user flexibility of system design. The families also supports low data retention voltage for battery back-up operation with low data retention current.

### PRODUCT FAMILY

| Product Family | Operating Temperature | Vcc Range | Speed(ns) | Power Dissipation | | PKG Type |
|---|---|---|---|---|---|---|
| | | | | Standby ($I_{SB1}$, Typ) | Operating ($I_{CC1}$, Max) | |
| K6F2008S2E-F | Industrial(-40~85°C) | 2.3~2.7V | 70[1]/85ns | 0.5µA[2] | 2mA | 32-TSOP1-0813.4F |

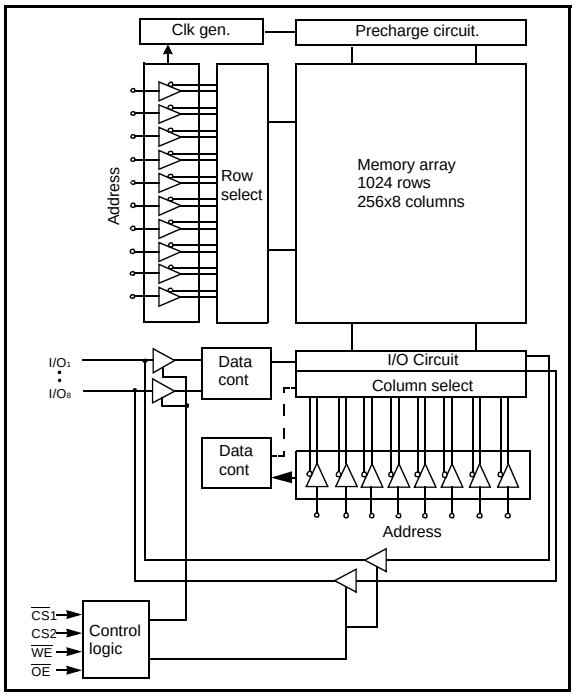
1. The parameter is measured with 30pF test load.
2. Typical value are measured at $V_{CC}$=2.5V, $T_A$=25°C, and not 100% tested.

### PIN DESCRIPTION




| Name | Function | Name | Function |
|---|---|---|---|
| $\overline{CS_1}$, $CS_2$ | Chip Select Input | $I/O_1$~$I/O_8$ | Data Inputs/Outputs |
| $\overline{OE}$ | Output Enable | Vcc | Power |
| $\overline{WE}$ | Write Enable Input | Vss | Ground |
| $A_0$~$A_{17}$ | Address Inputs | | |

### FUNCTIONAL BLOCK DIAGRAM




**SAMSUNG ELECTRONICS CO., LTD.** reserves the right to change products and specifications without notice.

## PRODUCT LIST

| Industrial Temperature Products(-40~85°C) | |
|---|---|
| **Part Name** | **Function** |
| K6F2008S2E-YF70<br>K6F2008S2E-YF85 | 32-sTSOP1-F, 70ns, 2.5V, LL<br>32-sTSOP1-F, 85ns, 2.5V, LL |

## FUNCTIONAL DESCRIPTION

| $\overline{CS_1}$ | $CS_2$ | $\overline{OE}$ | $\overline{WE}$ | I/O | Mode | Power |
|---|---|---|---|---|---|---|
| H | X[1)] | X[1)] | X[1)] | High-Z | Deselected | Standby |
| X[1)] | L | X[1)] | X[1)] | High-Z | Deselected | Standby |
| L | H | H | H | High-Z | Output Disable | Active |
| L | H | L | H | Dout | Read | Active |
| L | H | X[1)] | L | Din | Write | Active |

1. X means don't care (Must be high or low states)

## ABSOLUTE MAXIMUM RATINGS[1)]

| Item | Symbol | Ratings | Unit |
|---|---|---|---|
| Voltage on any pin relative to Vss | $V_{IN}$,$V_{OUT}$ | -0.2 to $V_{CC}$+0.3V | V |
| Voltage on Vcc supply relative to Vss | $V_{CC}$ | -0.2 to 3.0 | V |
| Power Dissipation | $P_D$ | 1.0 | W |
| Storage temperature | $T_{STG}$ | -65 to 150 | °C |
| Operating Temperature | $T_A$ | -40 to 85 | °C |

1. Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation should be restricted to recommended operating condition. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

## RECOMMENDED DC OPERATING CONDITIONS[1)]

| Item | Symbol | Min | Typ | Max | Unit |
|---|---|---|---|---|---|
| Supply voltage | Vcc | 2.3 | 2.5 | 2.7 | V |
| Ground | Vss | 0 | 0 | 0 | V |
| Input high voltage | $V_{IH}$ | 2.0 | - | Vcc+0.2[2)] | V |
| Input low voltage | $V_{IL}$ | -0.2[3)] | - | 0.6 | V |

Note:
1. Industrial Product: $T_A$=-40 to 85°C, unless otherwise specified.
2. Overshoot: Vcc+1.0V in case of pulse width≤20ns.
3. Undershoot: -1.0V in case of pulse width≤20ns.
4. Overshoot and undershoot are sampled, not 100% tested.

## CAPACITANCE[1)] (f=1MHz, $T_A$=25°C)

| Item | Symbol | Test Condition | Min | Max | Unit |
|---|---|---|---|---|---|
| Input capacitance | $C_{IN}$ | $V_{IN}$=0V | - | 8 | pF |
| Input/Output capacitance | $C_{IO}$ | $V_{IO}$=0V | - | 10 | pF |

1. Capacitance is sampled, not 100% tested

## DC AND OPERATING CHARACTERISTICS

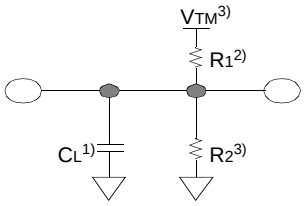
| Item | Symbol | Test Conditions | | Min | Typ[1)] | Max | Unit |
|---|---|---|---|---|---|---|---|
| Input leakage current | $I_{LI}$ | $V_{IN}$=Vss to Vcc | | -1 | - | 1 | µA |
| Output leakage current | $I_{LO}$ | $\overline{CS_1}$=$V_{IH}$ or $CS_2$=$V_{IL}$ or $\overline{OE}$=$V_{IH}$ or $\overline{WE}$=$V_{IL}$, $V_{IO}$=Vss to Vcc | | -1 | - | 1 | µA |
| Average operating current | $I_{CC1}$ | Cycle time=1µs, 100% duty, $I_{IO}$=0mA, $\overline{CS_1}$≤0.2V, $CS_2$≥Vcc-0.2V, $V_{IN}$≤0.2V or $V_{IN}$≥Vcc-0.2V | | - | - | 2 | mA |
| | $I_{CC2}$ | Cycle time=Min, 100% duty, $I_{IO}$=0mA, $\overline{CS_1}$=$V_{IL}$, $CS_2$=$V_{IH}$, $V_{IN}$=$V_{IL}$ or $V_{IH}$ | 85ns | - | - | 12 | mA |
| | | | 70ns | - | - | 15 | mA |
| Output low voltage | $V_{OL}$ | $I_{OL}$=0.5mA | | - | - | 0.4 | V |
| Output high voltage | $V_{OH}$ | $I_{OH}$=-0.5mA | | 2.0 | - | - | V |
| Standby Current(CMOS) | $I_{SB1}$ | Other inputs=Vss to Vcc<br>1) $\overline{CS_1}$≥Vcc-0.2V, CS2≥Vcc-0.2V($\overline{CS_1}$ controlled) or<br>2) 0V≤$CS_2$≤0.2V ($CS_2$ controlled) | | - | 0.5 | 5 | µA |

1. Typical value are measured at $V_{CC}$=2.5V, $T_A$=25°C, and not 100% tested.

## AC OPERATING CONDITIONS

**TEST CONDITIONS** (Test Load and Test Input/Output Reference)

Input pulse level: 0.4 to 2.2V
Input rising and falling time: 5ns
Input and output reference voltage: 1.1V
Output load (See right): $C_L$=100pF+1TTL
$C_L$=30pF+1TTL




1. Including scope and jig capacitance
2. $R_1$=3070Ω, $R_2$=3150Ω
3. $V_{TM}$ =2.3V

## AC CHARACTERISTICS(Vcc=2.3~2.7V, Industrial product: $T_A$=-40 to 85°C)

| Parameter List | | Symbol | Speed Bins | | | | Units |
|---|---|---|---|---|---|---|---|
| | | | 70ns[1] | | 85ns | | |
| | | | Min | Max | Min | Max | |
| Read | Read Cycle Time | $t_{RC}$ | 70 | - | 85 | - | ns |
| | Address Access Time | $t_{AA}$ | - | 70 | - | 85 | ns |
| | Chip Select to Output | $t_{CO}$ | - | 70 | - | 85 | ns |
| | Output Enable to Valid Output | $t_{OE}$ | - | 35 | - | 40 | ns |
| | Chip Select to Low-Z Output | $t_{LZ}$ | 10 | - | 10 | - | ns |
| | Output Enable to Low-Z Output | $t_{OLZ}$ | 5 | - | 5 | - | ns |
| | Chip Disable to High-Z Output | $t_{HZ}$ | 0 | 25 | 0 | 25 | ns |
| | Output Disable to High-Z Output | $t_{OHZ}$ | 0 | 25 | 0 | 25 | ns |
| | Output Hold from Address Change | $t_{OH}$ | 10 | - | 10 | - | ns |
| Write | Write Cycle Time | $t_{WC}$ | 70 | - | 85 | - | ns |
| | Chip Select to End of Write | $t_{CW}$ | 60 | - | 70 | - | ns |
| | Address Set-up Time | $t_{AS}$ | 0 | - | 0 | - | ns |
| | Address Valid to End of Write | $t_{AW}$ | 60 | - | 70 | - | ns |
| | Write Pulse Width | $t_{WP}$ | 50 | - | 60 | - | ns |
| | Write Recovery Time | $t_{WR}$ | 0 | - | 0 | - | ns |
| | Write to Output High-Z | $t_{WHZ}$ | 0 | 20 | 0 | 25 | ns |
| | Data to Write Time Overlap | $t_{DW}$ | 30 | - | 35 | - | ns |
| | Data Hold from Write Time | $t_{DH}$ | 0 | - | 0 | - | ns |
| | End Write to Output Low-Z | $t_{OW}$ | 5 | - | 5 | - | ns |

1. The parameter is measured with 30pF test load.

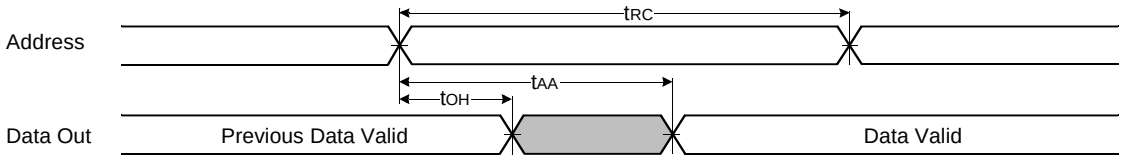
## DATA RETENTION CHARACTERISTICS

| Item | Symbol | Test Condition | Min | Typ[2] | Max | Unit |
|---|---|---|---|---|---|---|
| Vcc for data retention | $V_{DR}$ | $\overline{CS_1}$≥Vcc-0.2V[1] | 1.5 | - | 2.7 | V |
| Data retention current | $I_{DR}$ | Vcc=1.5V, $\overline{CS_1}$≥Vcc-0.2V[1] | - | 0.5 | 2 | µA |
| Data retention set-up time | $t_{SDR}$ | See data retention waveform | 0 | - | - | ns |
| Recovery time | $t_{RDR}$ | | $t_{RC}$ | - | - | |

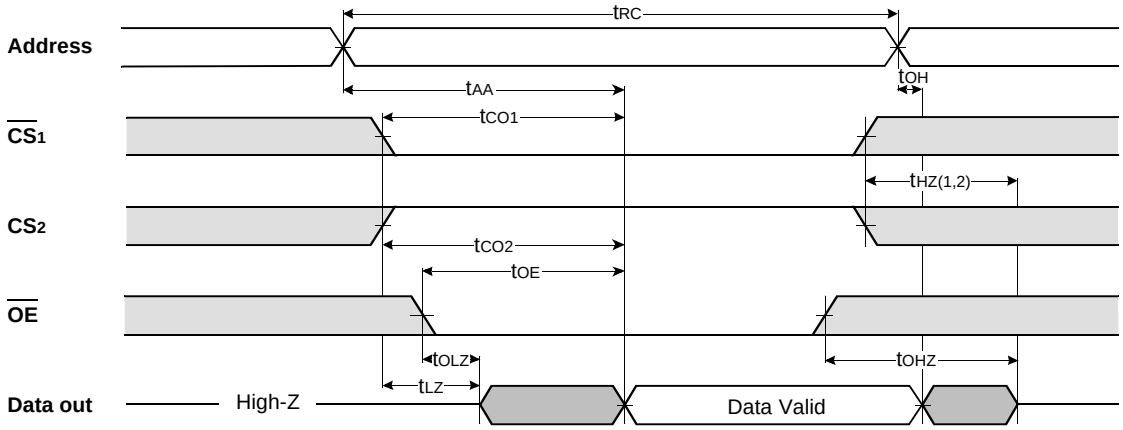
1. 1) $\overline{CS_1}$≥Vcc-0.2V, $CS_2$≥Vcc-0.2V($\overline{CS_1}$ controlled) or
   2) 0≤$CS_2$≤0.2V($CS_2$ controlled).
2. Typical value are measured at $T_A$=25°C and not 100% tested.

## TIMING DIAGRAMS

### TIMING WAVEFORM OF READ CYCLE(1) (Address Controlled, $\overline{CS_1}$=$\overline{OE}$=$V_{IL}$, $\overline{WE}$=$V_{IH}$)



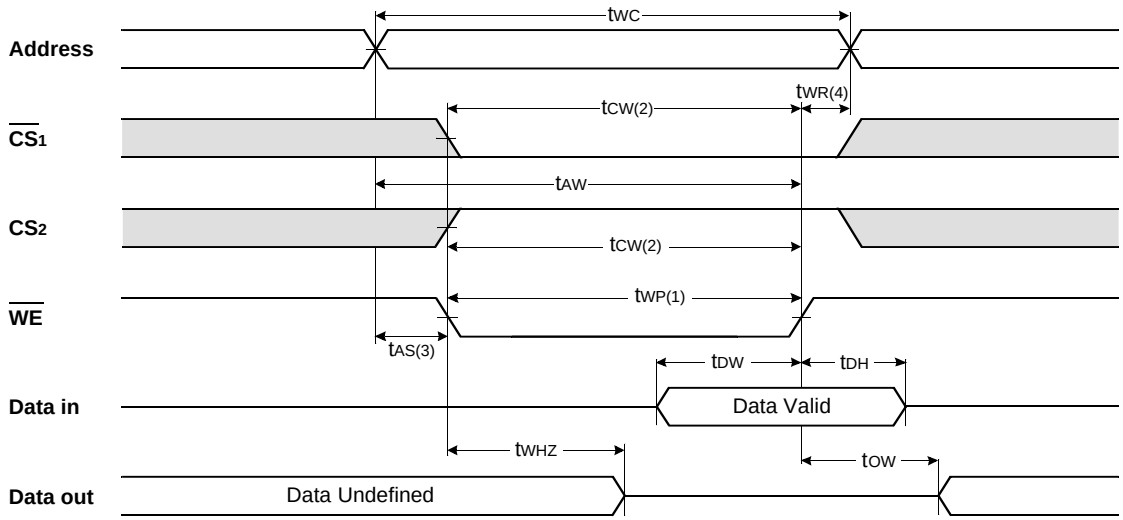

### TIMING WAVEFORM OF READ CYCLE(2) ($\overline{WE}$=$V_{IH}$)



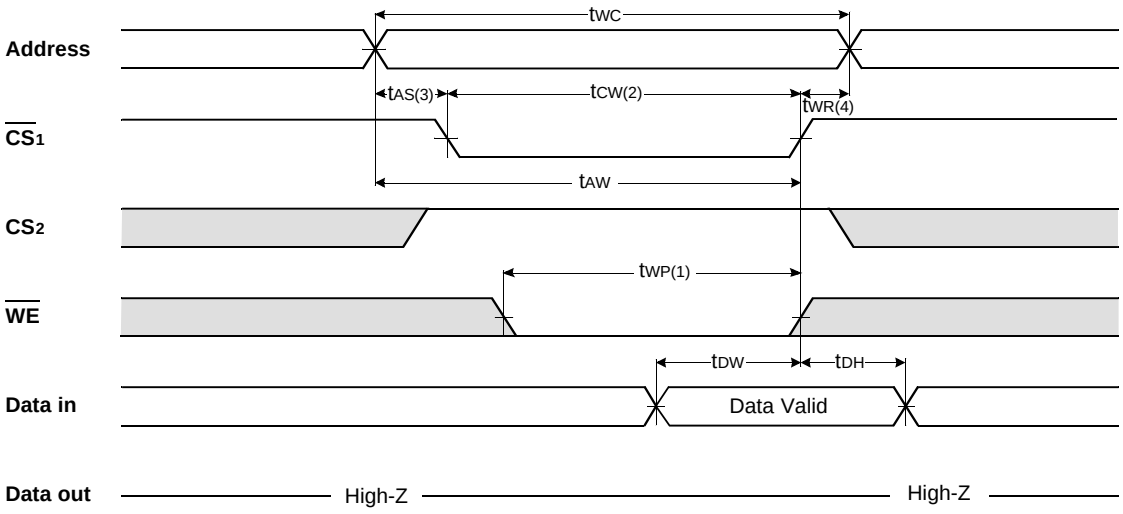

**NOTES** (READ CYCLE)

1. $t_{HZ}$ and $t_{OHZ}$ are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels.
2. At any given temperature and voltage condition, $t_{HZ}$(Max.) is less than $t_{LZ}$(Min.) both for a given device and from device to device interconnection.

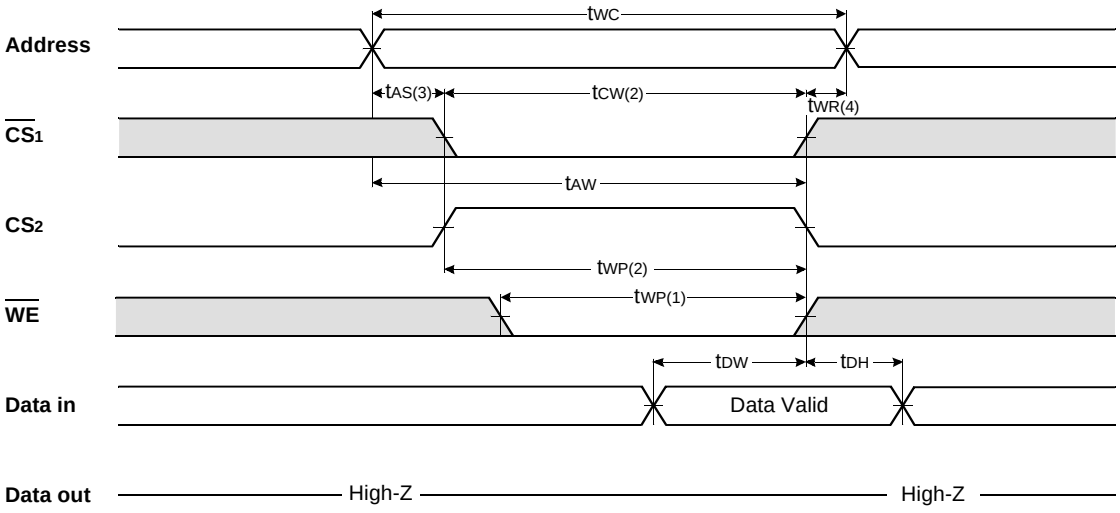
**TIMING WAVEFORM OF WRITE CYCLE(1)** ($\overline{WE}$ Controlled)




**TIMING WAVEFORM OF WRITE CYCLE(2)** ($\overline{CS_1}$ Controlled)



**TIMING WAVEFORM OF WRITE CYCLE(3)** ($CS_2$ Controlled)

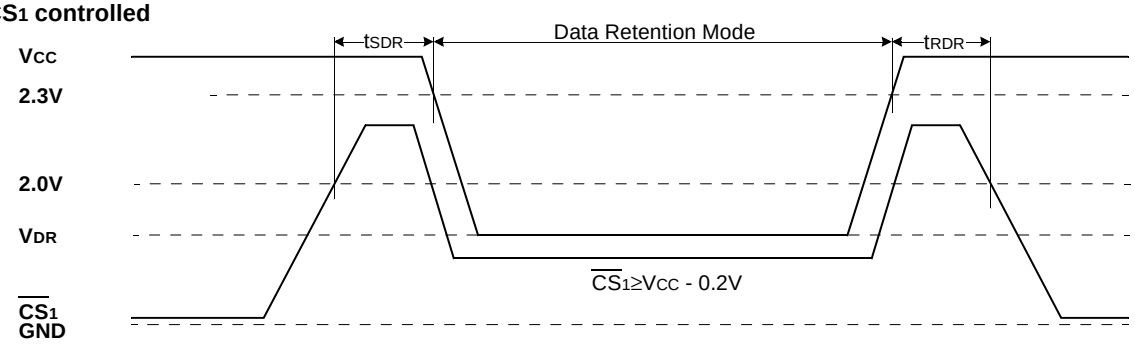



**NOTES** (WRITE CYCLE)

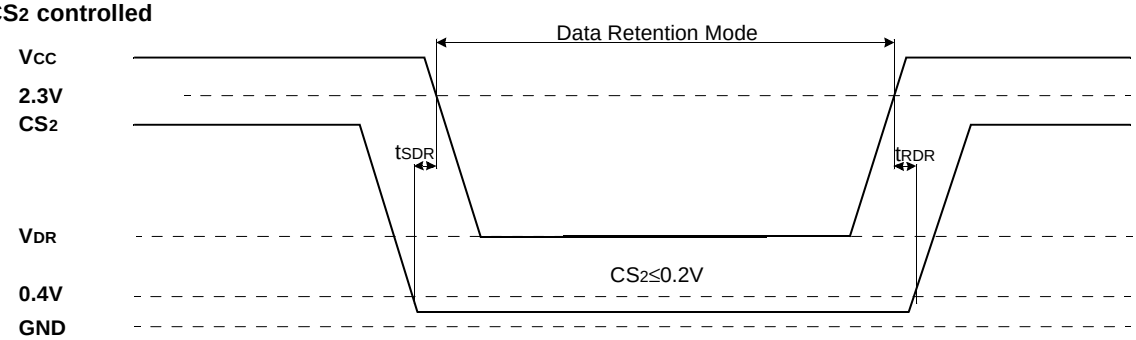
1. A write occurs during the overlap of a low $\overline{CS_1}$, a high $CS_2$ and a low $\overline{WE}$. A write begins at the latest transition among $\overline{CS_1}$ goes low, $CS_2$ going high and $\overline{WE}$ going low : A write end at the earliest transition among $\overline{CS_1}$ going high, $CS_2$ going low and $\overline{WE}$ going high, $t_{WP}$ is measured from the begining of write to the end of write.
2. $t_{CW}$ is measured from the $\overline{CS_1}$ going low or $CS_2$ going high to the end of write.
3. $t_{AS}$ is measured from the address valid to the beginning of write.
4. $t_{WR}$ is measured from the end of write to the address change. $t_{WR(1)}$ applied in case a write ends as $\overline{CS_1}$ or $\overline{WE}$ going high $t_{WR(2)}$ applied in case a write ends as $CS_2$ going to low.

## DATA RETENTION WAVE FORM

**$\overline{CS_1}$ controlled**




**$CS_2$ controlled**



## PACKAGE DIMENSIONS

Units: millimeters(inches)

### 32 PIN THIN SMALL OUTLINE PACKAGE TYPE I (0813.4F)

